# **SKD 51**



### **Power Bridge Rectifiers**

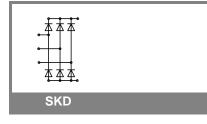
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### Features

- Glass passivated silicon chips
- Fast-on terminals for pcb solder or plug on connections
- Sturdy insulated metal base plate
- Low thermal impedance through use of direct copper bonded aluminum substrate
- Blocking voltage up to 1800V
- High surge currents
- UL recognized, file no. E63 532

### **Typical Applications\***

- Three phase rectifier for power supplies
- Input rectifier for variable frequency drives
- Rectifier for DC motor field supplies
- Battery charger rectifiers
- Recommended snubber network: RC: 0.1  $\mu$ F, 50  $\Omega$  (P <sub>R</sub> = 1 W)
- For solder connection. Permissible current for plug connection see DIN IEC 760E and DIN 46249 part 1
- 2) Freely suspended or mounted on an insulator
- Mounted on a painted metal sheet of min.
  250 x 250 x 1 mm

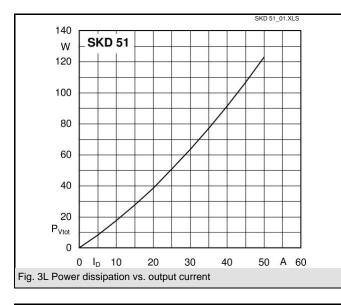


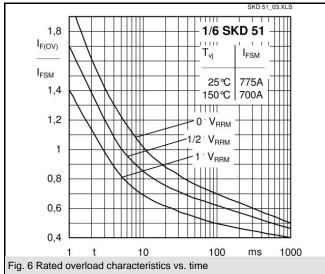
V <sub>RSM</sub>	V <sub>RRM</sub> , V <sub>DRM</sub>	$I_D = 50^{11} A$ (full conduction)
V	V	(T <sub>c</sub> = 127 °C)
500	400	SKD 51/04
900	800	SKD 51/08
1300	1200	SKD 51/12
1500	1400	SKD 51/14
1700	1600	SKD 51/16
1900	1800	SKD 51/18

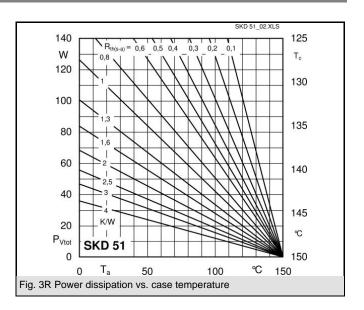
Symbol	Conditions	Values	Units
I <sub>D</sub>	T <sub>c</sub> = 127 °C	50	А
-	$T_a = 45 \text{ °C}; \text{ isolated } ^2)$	7	А
	$T_a = 45 \text{ °C}; \text{ chassis } ^{3)}$	18	А
	T <sub>a</sub> = 45 °C; R4A/120	27	А
	T <sub>a</sub> = 45 °C; P5A/100	31	A
I <sub>FSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	775	А
	T <sub>vi</sub> = 150 °C; 10 ms	700	А
i²t	T <sub>vi</sub> = 25 °C; 8,3 10 ms	3000	A²s
	T <sub>vj</sub> = 150 °C; 8,3 10 ms	2450	A²s
V <sub>F</sub>	T <sub>vi</sub> = 25 °C; I <sub>F</sub> = 75 A	max. 1,45	V
V <sub>(TO)</sub>	T <sub>vi</sub> = 150 °C	max. 0,8	V
r <sub>T</sub>	T <sub>vi</sub> = 150 °C	max. 8,5	mΩ
I <sub>RD</sub>	$T_{vj} = 25 \text{ °C}; V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$	max. 0,2	mA
	T <sub>vj</sub> = 150 °C; V <sub>RD</sub> = V <sub>RRM</sub>	4	mA
t <sub>rr</sub>	T <sub>vj</sub> = 25 °C; I <sub>F</sub> = I <sub>R</sub> = 1A	5	μs
R <sub>th(j-c)</sub>	per diode	1,1	K/W
	total	0,183	K/W
R <sub>th(c-s)</sub>	total	0,1	K/W
R <sub>th(j-a)</sub>	isolated <sup>2)</sup> (chassis <sup>3)</sup> )	9 (3,15)	K/W
T <sub>vj</sub>		- 40 +150	°C
T <sub>stg</sub>		- 40 +125	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 ( 3000 )	V
Ms	to heatsink	4,5 ± 15 %	Nm
M <sub>t</sub>			
m		97	g
Case		G 51	

#### 26-06-2007 SCH

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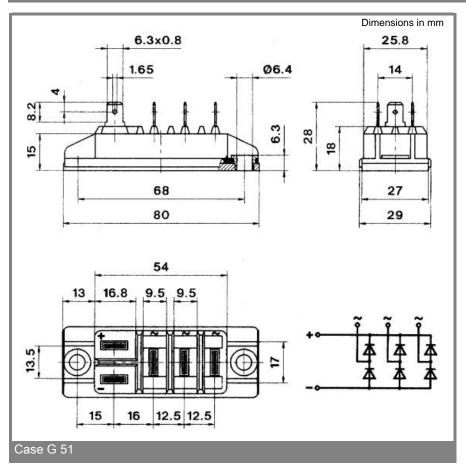






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